

# SAIP 2011



Contribution ID : 42

## **The Infrared Plasma Resonance of P in SiC**

Wednesday 13 Jul 2011 at 17:00 (02h00')

### **Content :**

The concentration of any dopant in a semiconductor can usually easily and readily be established using the plasma resonance minimum. Infrared reflectance spectroscopy was used to assess the doping of SiC wafers by phosphor implantation. However, results obtained did not match the theoretical predictions. The problem was investigated, including an assessment of the applicable theory. Results will be presented and discussed.

### **Level (Hons, MSc, PhD, other)? :**

other

### **Consider for a student award (Yes / No)? :**

No

### **Short Paper :**

No

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**Session classification :** Poster1

**Track classification :** Track A - Condensed Matter Physics and Material Science

**Type :** Poster Presentation